

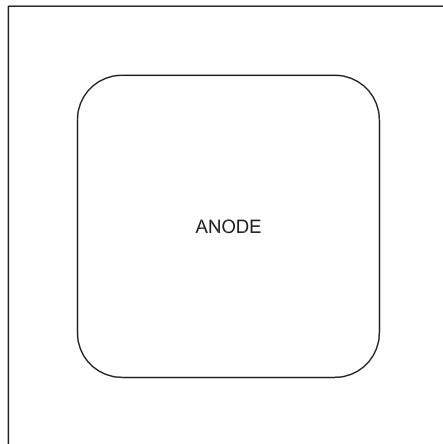
PROCESS CPD24
Fast Recovery Rectifier
1 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	11 MILS
Anode Bonding Pad Area	35 x 35 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE R1

GROSS DIE PER 4 INCH WAFER

4,250

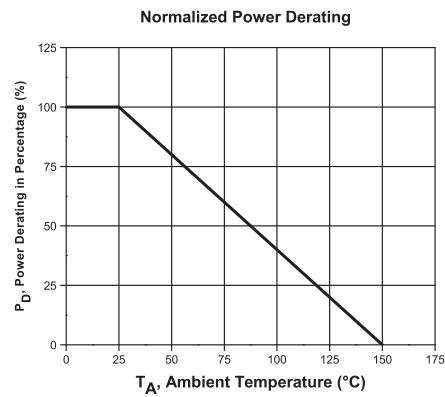
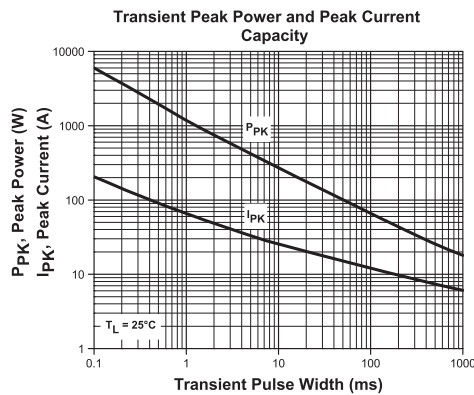
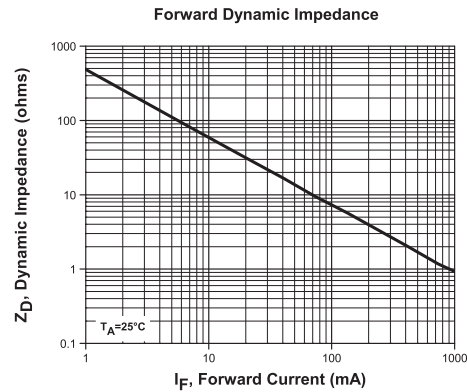
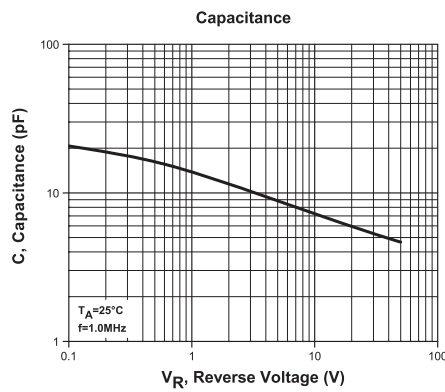
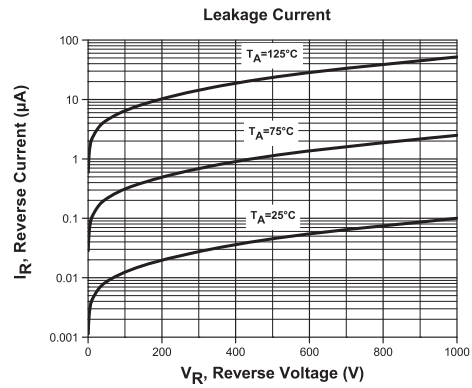
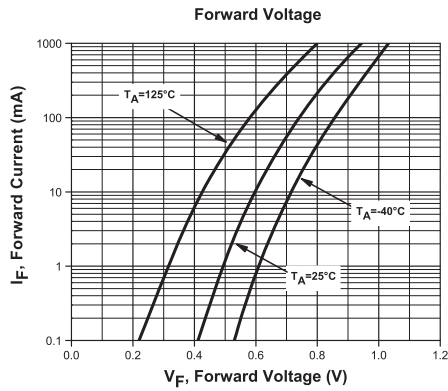
PRINCIPAL DEVICE TYPES

1N4933 thru 1N4937
1N4942 thru 1N4948
1N5615 thru 1N5623
CMR1F-02M Series

R3 (29-April 2010)

PROCESS CPD24

Typical Electrical Characteristics



R3 (29-April 2010)